

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A thermal treatment system for semiconductors, comprising:

an outer tube, comprising silicon carbide, and which has an upper portion closed and a lower portion opened, and has a flange formed on an outer peripheral side of the lower portion;

a base, which supports the lower portion of the outer tube and provides a hermetic seal between the lower portion of the outer tube and the base;

a lid, which is provided so as to selectively open and close an opening formed in a central portion of the base; and

a reactor wall, which surrounds an outer peripheral wall and an upper wall of the outer tube and has a heater provided on an inner side;

wherein an annular sealing member and an annular supporting member are interposed between the outer tube and the base so that the supporting member is located around an outer peripheral side of the sealing member, and wherein the supporting member has an effective heat transfer coefficient of 50 to 2,000 W/(m²·K), and

the supporting member comprises plural members layered in a height direction or a peripheral direction.

Claim 2 (Original): The thermal treatment system according to Claim 1, wherein the supporting member has an effective heat transfer coefficient of 50 to 1,000 W/(m²·K).

Claim 3 (Canceled).

Claim 4 (Previously Presented): The thermal treatment system according to Claim 1, wherein the supporting member comprises a fluororesin or aluminum.

Claim 5 (Previously Presented): The thermal treatment system according to Claim 1, wherein there is included an inner tube, which is provided around an inner peripheral side of the outer tube with a gap, which has upper and lower ends opened, and which comprises silicon carbide.